

SWITCHING DIODE

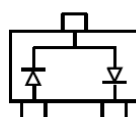
FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

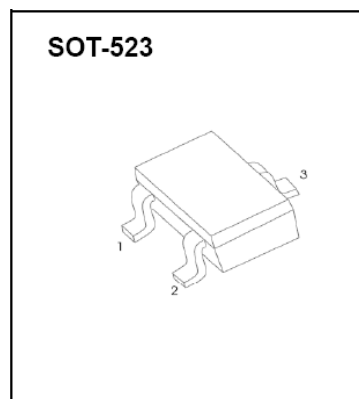


BAW56T

BAV70T



BAV99T



Maximum Ratings @Ta=25℃

Parameter	Symbol	Limit	Unit
Reverse voltage	V_R	85	V
Forward current	I_O	75	mA
Forward power dissipation	P_D	150	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55~+150	℃

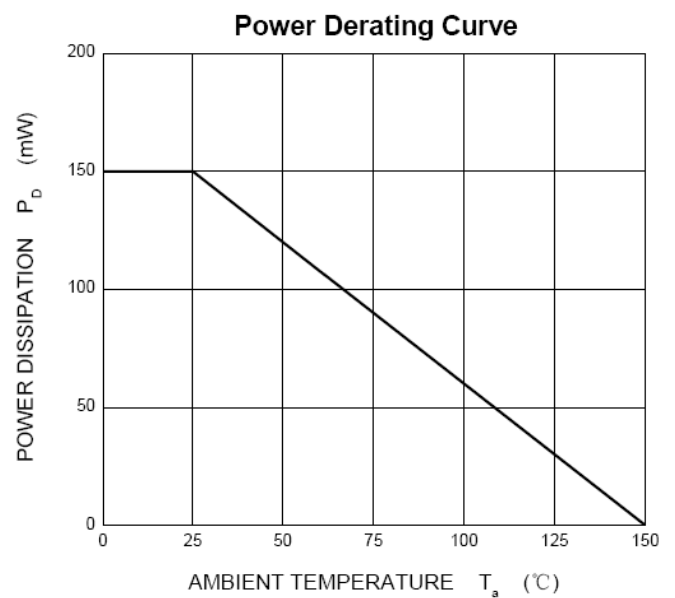
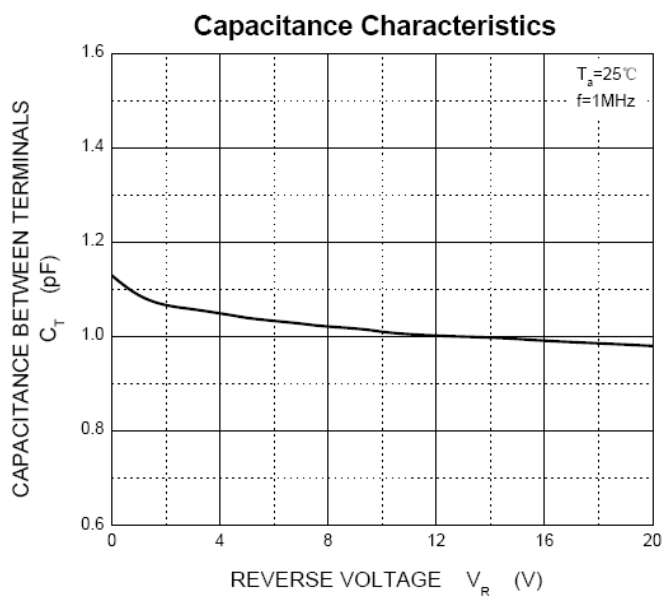
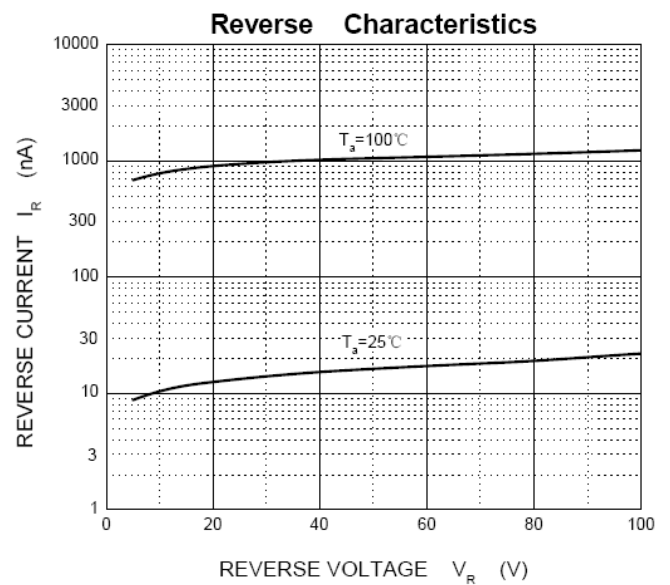
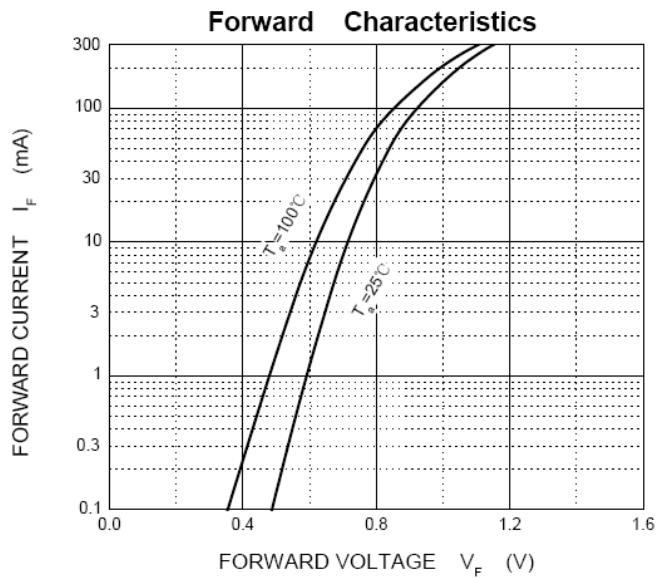
ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 1\mu A$	85		V
Reverse voltage leakage current	I_{R1}	$V_R = 75V$		2	μA
	I_{R2}	$V_R = 25V$		0.03	μA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 10mA$ $I_F = 50mA$ $I_F = 150mA$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R = 0$ $f = 1MHz$		1.5	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10mA$ $I_{rr} = 0.1 \times I_R, R_L = 100\Omega$		4	ns



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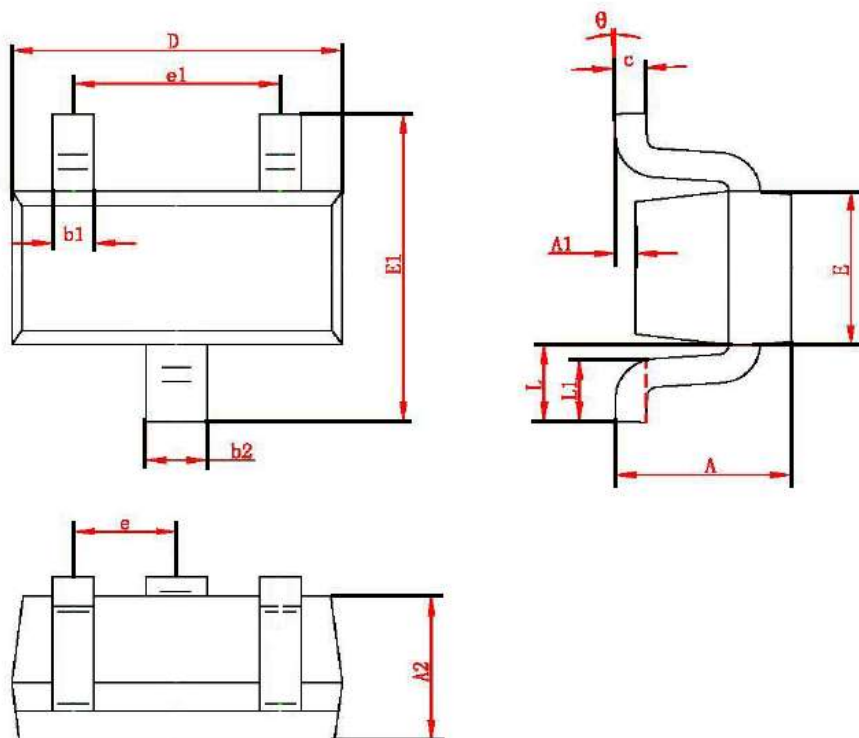
Typical Characteristics





BAW56T BAV70T BAV99T

SOT-523 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°